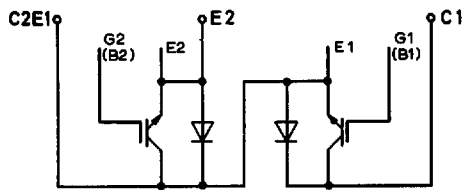
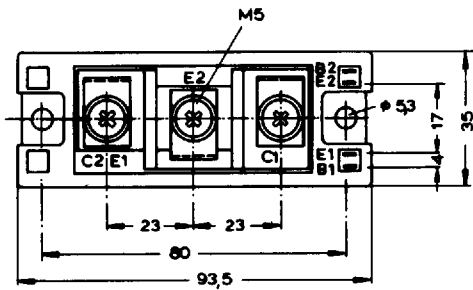
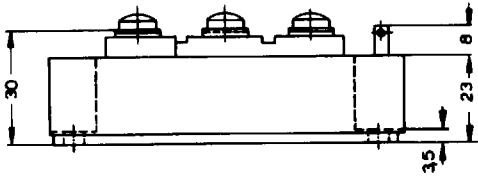


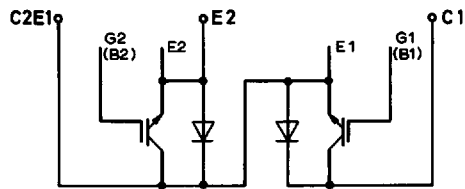
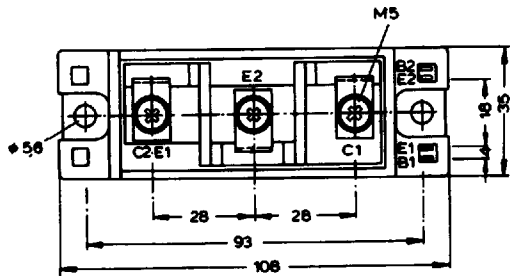
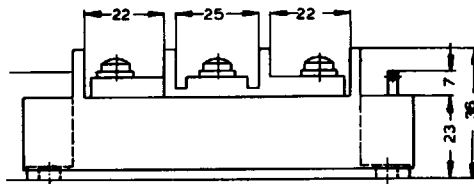
Transistor		Transistor		Thermische Eigenschaften		Thermal properties	
Elektrische Eigenschaften		Electrical properties		R _{thJC}	DC, pro Baustein / per module DC, pro Zweig / per arm	0,07 °C/W 0,417 °C/W	
Höchstzulässige Werte		Maximum rated values					
V _{CES}		600	V	t _{vjmax}		150	°C
I _C		100	A	t _{vjop}		-40 / +150	°C
I _{CRM}	t _p = 1 ms	200	A	t _{stg}		-40 / +125	°C
P _{tot}	t _C = 25°C	300	W	Inversdiode		Inverse diode	
V _{GE}		20	V	Elektrische Eigenschaften		Electrical properties	
V _{EG}		20	V	Höchstzulässige Werte		Maximum rated values	
Charakteristische Werte		Characteristic values		I _{F (max)}		100	A
V _{CE sat}	i _{CM} = 100 A, v _{GE} = 15 V, t _{vj} = 25°C typ. 3 V i _{CM} = 100 A, v _{GE} = 15 V, t _{vj} = 25°C max. 4 V			I _{FRM}	t _p = 1 ms	200	A
V _{GE (th)}	v _{CE} = 5 V, i _C = 100 mA, t _{vj} = 25°C min. 3 V v _{CE} = 5 V, i _C = 100 mA, t _{vj} = 25°C max. 6 V			Charakteristische Werte		Characteristic values	
C _{GE}	v _{CE} = 10 V, v _{GE} = 0 V f _o = 1 MHz, t _{vj} = 25°C typ. 7,4 nF			v _F	i _F = 100 A, v _{GE} = 0 V, t _{vj} = 25°C typ. 1,8 V i _F = 100 A, v _{GE} = 0 V, t _{vj} = 25°C max. 2,7 V		
i _{CES}	v _{CE} = 600 V, v _{GE} = 0 V, t _{vj} = 25°C typ. 0,5 mA v _{CE} = 600 V, v _{GE} = 0 V, t _{vj} = 125°C typ. 4 mA			I _{RM}	i _{FM} = 100 A, -di _F /dt = 100 A/μs v _{EG} = 10 V, t _{vj} = 25°C typ. 13 A i _{FM} = 100 A, -di _F /dt = 100 A/μs v _{EG} = 10 V, t _{vj} = 125°C typ. 22 A		
i _{GES}	v _{GE} = 20 V, t _{vj} = 25°C typ. 50 nA v _{GE} = 20 V, t _{vj} = 25°C max. 500 nA			Q _r	i _{FM} = 100 A, -di _F /dt = 100 A/μs v _{EG} = 10 V, t _{vj} = 25°C typ. 2 μAs i _{FM} = 100 A, -di _F /dt = 100 A/μs v _{EG} = 10 V, t _{vj} = 125°C typ. 6 μAs		
i _{EGS}	v _{EG} = 20 V, t _{vj} = 25°C typ. 50 nA v _{EG} = 20 V, t _{vj} = 25°C max. 500 nA			Thermische Eigenschaften		Thermal properties	
t _{on}	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, R _G = 24 Ω, t _{vj} = 25°C typ. 0,4 μs i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, R _G = 24 Ω, t _{vj} = 125°C typ. 0,5 μs			R _{thJC}	DC, pro Baustein / per module DC, pro Zweig / per arm	0,21 °C/W 1,25 °C/W	
t _s	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 25°C typ. 0,4 μs i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 125°C typ. 0,5 μs			t _{vjmax}		125	°C
t _f	i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 25°C typ. 0,15 μs i _{CM} = 100 A, v _{CE} = 300 V, v _{LF} = 15 V, v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 125°C typ. 0,25 μs			t _{vjop}		-40 / +125	°C
Bedingungen für den Kurzschlußschutz		Conditions for protection against short circuits		t _{stg}		-40 / +125	°C
t _{fg} = 10 μs, v _{LF} = v _{LR} = 15 V, R _G = 24 Ω, t _{vj} = 125°C,		V _{CC} = 350 V, V _{CEM} = 500 V, i _{CMK1} ≈ 500 A, i _{CMK2} ≈ 350 A		Innere Isolation		Internal insulation	
				Isoliermaterial: AlN V _{ISOL} RMS		Insulating material: AlN 2,5 kV	
				Mechanische Eigenschaften		Mechanical properties	
				G		500	g
				M1		3	Nm
				M2		3	Nm
				Maßbild Seite 124, Nr. 10		outline page 124, no. 10	

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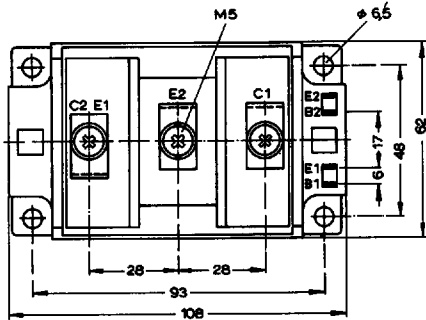
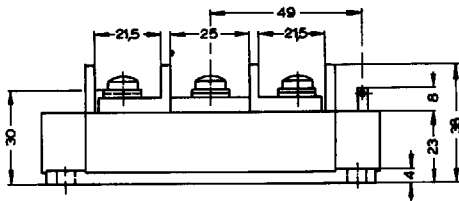
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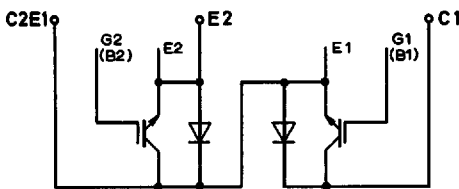
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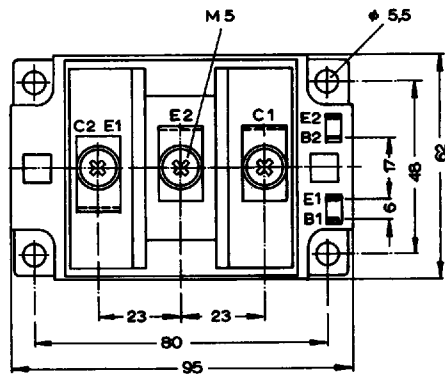
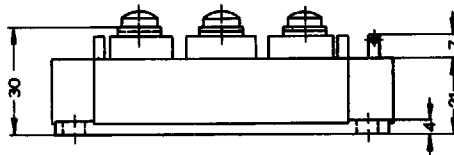


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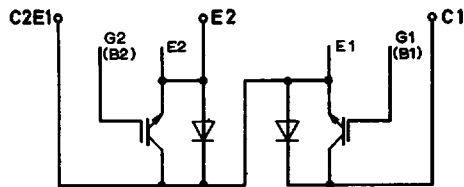


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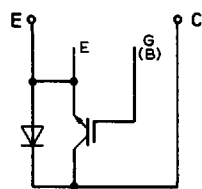
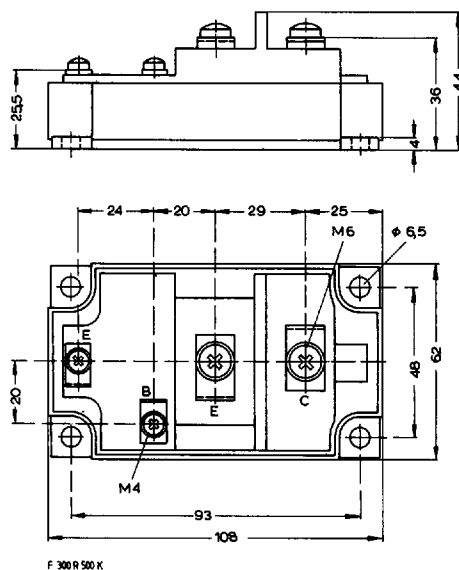
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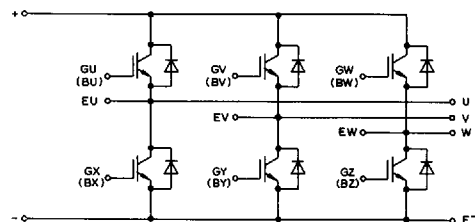
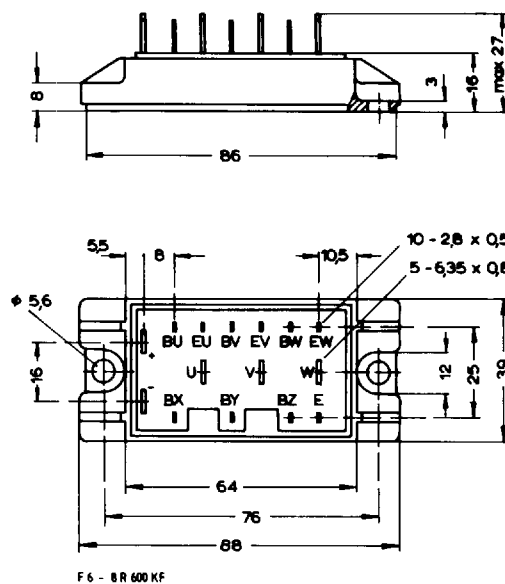
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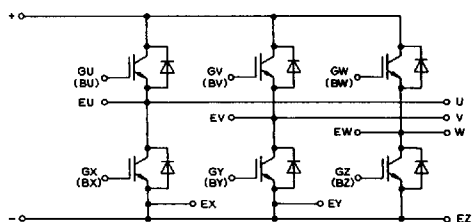
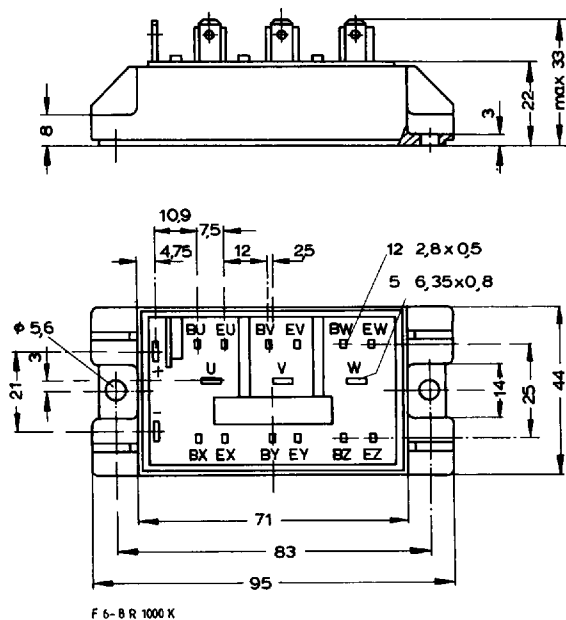
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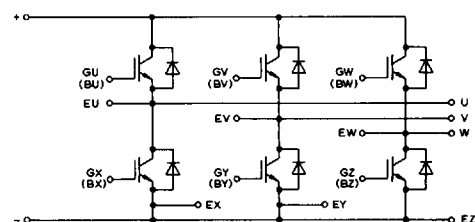
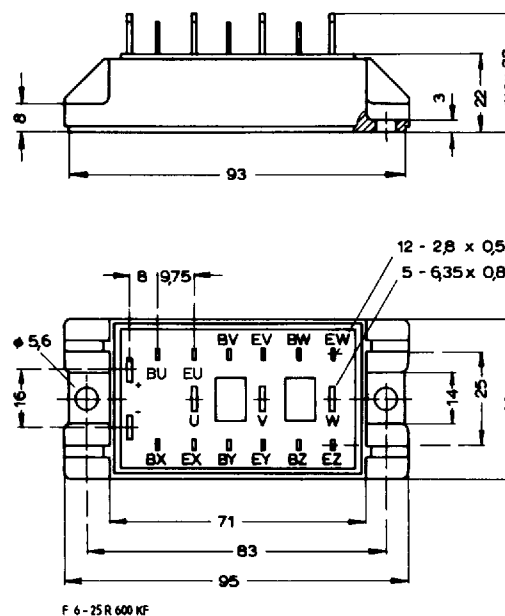
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6



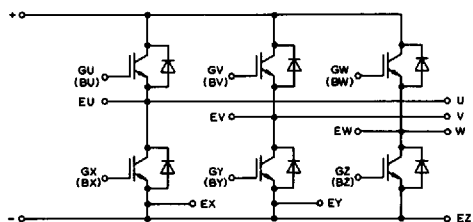
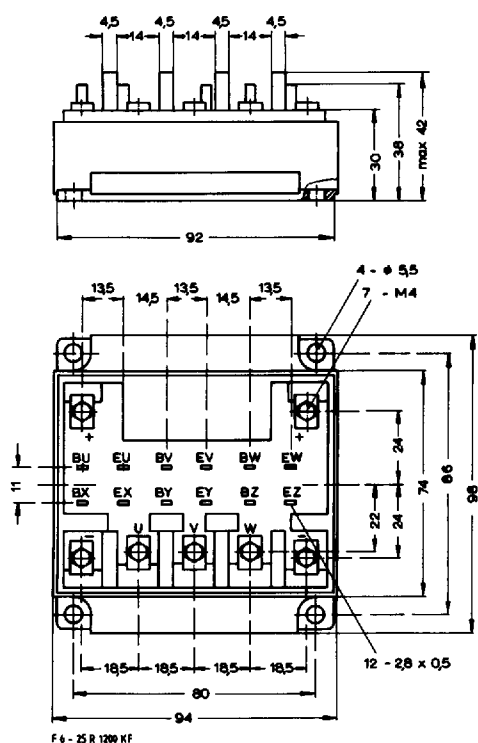
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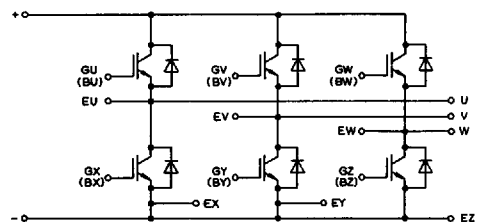
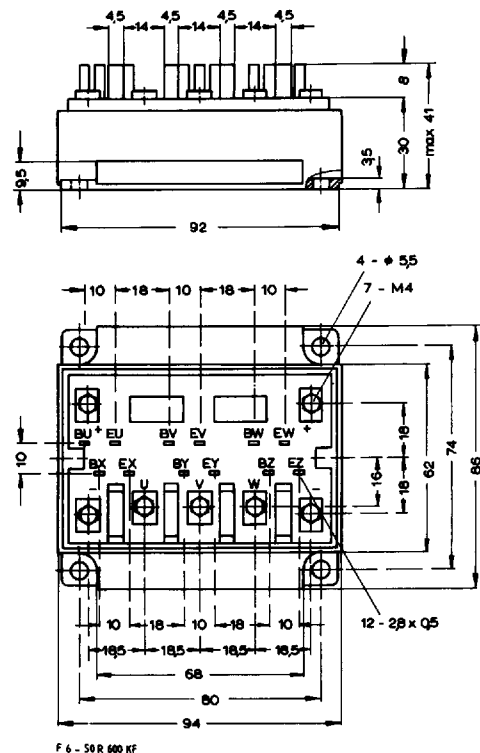
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